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In-growth Test for Monolithic 3D Integrated SRAM

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Advantages of Monolithic 3D Integration



Challenge on Test Method of M3I SRAM Testability Problem Incomplete circuit components and untestable Unable to adding redundant transistors. Unable to repair a fault cell with a redundancy cell Unknown reparability before fabrication finishes

Overview of Proposed Test Methodology



Composing & Testing

- A novel Design-for-Testability method enables the proposed In-growth test on cell-level ack of Efficient Pre-Bond Test Method. & High Overall Fabrication Cost



partitioned incomplete SRAM cells. Early Stop

- A judgement factor & a statistical cost model determine whether to stop the fabrication

Design-for-Testability Method to Make Incomplete SRAM Cells Testable during Fabrication



- nMOS and pMOS transistors are fabricated on the same tier instead of traditionally being splitted into two adjacent tiers.
- Transistors are composed into <u>a temporary</u> <u>SRAM cell</u> with additional <u>metal wires</u> connecting the transistors.
- Before fabricating the top tier, the additional metal wires are etched away.

— Word-line

Bit-line

nMOS Transistors

pMOS Transistors





Experiment Results: The Effectiveness & The Better Performance with More Layers

Applying to multi-tiers Effectiveness of the Sweet Point Accuracy of the model CMOS-based / F=3.0% R: 8 CMOS-based / F=1.5% CMOS-based / F=3.0% CMOS-based / F=3.0% CMOS-based / F=1.5% 2.4 ■ 2-tier ■ 4-tier ■ 6-tier ■ 2-tier ■ 4-tier ■ 6-tier -Statistical Val **SP 50% 100% SP 50% 100%** 1.2 1.4 1.4 tso 2.2 2 2 1.8 ---Simulative Value Cost Cost Cost 1.2 1.2 ost Normalized 1.6 1.4 1.2 1.2 0.8 0.6 Normalized 0.6 0.4 0.2 alized Б aliz **Silem 0.6** 0.4 0.2 0.4 No. 5 Ž 0.2 0.4 30 32 34 22 24 26 28 50 52 54 56 58 60 16 18 20 22 24 26 28 30 18 20 22 24 26 28 30 40 42 44 46 48 10 12 50 52 54 56 58 60 10 12 14 16 Threshold Redundancy Redundancy Redundancy Redundancy Normalized Cost – The cost of the conventional test methodology testing the whole M3I SRAM after the fabrication process finishes. **R** - Redundancy columns of every layer **F** - Fault rate Threshold - A threshold value of the redundancy requirements as judgement factor, derived from the test results of the bottom tier, to judge whether to "early stop".

SP - By building a statistical model of cost, we provide a best threshold setting (denoted as "sweet point", SP), which reaches the minimum overall cost.